

SÃ©bastien Francoeur

List of Publications by Year in descending order

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62
papers

3,750
citations

361045

20
h-index

168136

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63
all docs

63
docs citations

63
times ranked

4652
citing authors

#	ARTICLE	IF	CITATIONS
1	Visible Out-of-plane Polarized Luminescence and Electronic Resonance in Black Phosphorus. Nano Letters, 2022, , .	4.5	5
2	Superconductor-based quaternary photonic crystals for high sensitivity temperature sensing. Chinese Journal of Physics, 2022, 77, 176-188.	2.0	13
3	Out-of-Plane Polarized Visible Luminescence and Electronic Resonance in Black Phosphorus. ECS Meeting Abstracts, 2022, MA2022-01, 852-852.	0.0	0
4	Tunable polychromatic filters based on semiconductor-superconductor-dielectric periodic and quasi-periodic hybrid photonic crystal. Optical Materials, 2021, 111, 110690.	1.7	15
5	(Invited) Raman Spectroscopy of Confined Hyperbolic and Surface Phonon-Polaritons in 2D Materials. ECS Meeting Abstracts, 2021, MA2021-01, 599-599.	0.0	0
6	Disentangling phonon channels in nanoscale heat transport. Physical Review B, 2021, 104, .	1.1	0
7	Restoring the Coherence of Quantum Emitters through Optically Driven Motional Narrowing Forces. Nano Letters, 2021, 21, 10193-10198.	4.5	1
8	Mid-infrared Polarized Emission from Black Phosphorus Light-Emitting Diodes. Nano Letters, 2020, 20, 3651-3655.	4.5	69
9	(Invited) Rich Electron-Phonon Interactions in Atomically-Thin Black Phosphorus. ECS Meeting Abstracts, 2020, MA2020-01, 746-746.	0.0	0
10	Spectral Responsivity and Photoconductive Gain in Thin Film Black Phosphorus Photodetectors. ACS Photonics, 2019, 6, 3092-3099.	3.2	21
11	Second-Order Raman Scattering in Exfoliated Black Phosphorus. Nano Letters, 2018, 18, 1018-1027.	4.5	32
12	Energy reversal of light- and heavy-hole excitons bound to isoelectronic centers. Physical Review B, 2018, 98, .	1.1	3
13	Oxidation dynamics of ultrathin GaSe probed through Raman spectroscopy. Applied Physics Letters, 2017, 110, .	1.5	61
14	High-Fidelity and Ultrafast Initialization of a Hole Spin Bound to a Te Isoelectronic Center in ZnSe. Physical Review Letters, 2016, 117, 167401.	2.9	6
15	Polarization-Resolved Raman Study of Bulk-like and Davydov-Induced Vibrational Modes of Exfoliated Black Phosphorus. Nano Letters, 2016, 16, 7761-7767.	4.5	59
16	Light- and heavy-hole trions bound to isoelectronic centers. Physical Review B, 2015, 92, .	1.1	4
17	Dynamics of excitons bound to nitrogen isoelectronic centers in GaAs. Physical Review B, 2015, 91, .	1.1	9
18	Field effect tuning of microwave Faraday rotation and isolation with large-area graphene. Applied Physics Letters, 2015, 107, 093106.	1.5	10

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19	Photooxidation and quantum confinement effects in exfoliated black phosphorus. <i>Nature Materials</i> , 2015, 14, 826-832.	13.3	1,149
20	Phonon Engineering in Isotopically Disordered Silicon Nanowires. <i>Nano Letters</i> , 2015, 15, 3885-3893.	4.5	36
21	Comparison of EMCCD post-processing methods for photon counting flux ranges. <i>Proceedings of SPIE</i> , 2014, , .	0.8	0
22	Recombination dynamics of excitons bound to nitrogen isoelectronic centers in δ -doped GaP. <i>Physical Review B</i> , 2014, 89, .	1.1	4
23	Complete quantum control of exciton qubits bound to isoelectronic centres. <i>Nature Communications</i> , 2014, 5, 3980.	5.8	18
24	Photoluminescence from single nitrogen isoelectronic centers in gallium phosphide produced by ion implantation. <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	3
25	Plasmonic enhancement of the magneto-optical response of MnP nanoclusters embedded in GaP epilayers. <i>Physical Review B</i> , 2012, 86, .	1.1	9
26	Excitonic fine structure of out-of-plane nitrogen dyads in GaAs. <i>Journal of Luminescence</i> , 2011, 131, 2339-2341.	1.5	4
27	Charged excitons and biexcitons bound to isoelectronic centers. <i>Physical Review B</i> , 2010, 82, .	1.1	18
28	Band gap of sphalerite and chalcopyrite phases of epitaxial ZnSnP ₂ . <i>Applied Physics Letters</i> , 2010, 96, .	1.5	34
29	Effects of symmetry-breaking perturbations on excitonic states bound to systems of reduced symmetry. <i>Journal of Applied Physics</i> , 2010, 108, 043710.	1.1	12
30	Giant magneto-optical Faraday effect in GaP epilayers containing MnP magnetic nanoclusters. <i>Journal of Applied Physics</i> , 2010, 107, 09A949.	1.1	11
31	Excitons bound to Te isoelectronic dyads in ZnSe. <i>Physical Review B</i> , 2010, 82, .	1.1	13
32	Single nitrogen dyad magnetoluminescence in GaAs. <i>Physical Review B</i> , 2009, 80, .	1.1	13
33	High spatial resolution confocal microscope with independent excitation and detection scanning capabilities. <i>Review of Scientific Instruments</i> , 2009, 80, 063101.	0.6	6
34	Bi isoelectronic impurities in GaAs. <i>Physical Review B</i> , 2008, 77, .	1.1	77
35	Giant Spin-Orbit Bowing in GaAs _{1-x} Bi _x . <i>Physical Review Letters</i> , 2006, 97, 067205.	2.9	386
36	Bi-induced vibrational modes in GaAsBi. <i>Superlattices and Microstructures</i> , 2005, 37, 394-400.	1.4	29

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37	Band gaps of the dilute quaternary alloys $\text{Ga}_x\text{As}_{1-x}\text{Bi}_y$ and $\text{Ga}_{1-y}\text{In}_y\text{N}_x\text{As}_x$. Applied Physics Letters, 2005, 86, 112113.	1.5	66
38	Physics of Isoelectronic Dopants in GaAs. , 2005, , 179-221.		8
39	Ion beam characterization of $\text{GaAs}_{1-x}\text{Bi}_x$ epitaxial layers. Nuclear Instruments & Methods in Physics Research B, 2004, 219-220, 671-675.	0.6	20
40	Optical Spectroscopy of Single Impurity Centers in Semiconductors. Physical Review Letters, 2004, 93, 067403.	2.9	63
41	Band gap of $\text{GaAs}_{1-x}\text{Bi}_x$, $0 < x < 3.6\%$. Applied Physics Letters, 2003, 82, 3874-3876.	1.5	395
42	Molecular beam epitaxy growth of $\text{GaAs}_{1-x}\text{Bi}_x$. Applied Physics Letters, 2003, 82, 2245-2247.	1.5	425
43	Origin of the nitrogen-induced optical transitions in $\text{GaAs}_{1-x}\text{N}_x$. Physical Review B, 2003, 68, .	1.1	20
44	Observation of large optical anisotropy and valence band splitting in AlInAs self-assembled lateral quantum wells. Applied Physics Letters, 2002, 80, 243-245.	1.5	21
45	Two-dimensional array of self-assembled AlInAs quantum wires. Applied Physics Letters, 2002, 81, 529-531.	1.5	5
46	Initiation and evolution of phase separation in heteroepitaxial InAlAs films. Applied Physics Letters, 2002, 80, 3292-3294.	1.5	29
47	Optical properties of self-assembled lateral superlattices in AlInAs epitaxial layers and AlAs/InAs short-period superlattices. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 88, 118-124.	1.7	4
48	Electronic Structure of Heavily and Randomly Nitrogen Doped GaAs near the Fundamental Band Gap. Physica Status Solidi (B): Basic Research, 2001, 228, 287-291.	0.7	3
49	In situ Pyrometric Interferometry For Molecular Beam Epitaxy of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ on Si (111). Materials Research Society Symposia Proceedings, 2000, 639, 6571.	0.1	0
50	High Quality AlN and GaN Grown on Si(111) by Gas Source Molecular Beam Epitaxy with Ammonia. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 467-473.	1.0	3
51	Quantitative determination of the order parameter in epitaxial layers of ZnSnP_2 . Applied Physics Letters, 2000, 76, 2017-2019.	1.5	16
52	Optical properties of spontaneous lateral composition modulation in AlAs/InAs short-period superlattices. Applied Physics Letters, 2000, 77, 1765.	1.5	10
53	X-ray diffraction study of chalcopyrite ordering in epitaxial ZnSnP_2 grown on GaAs. Applied Physics Letters, 1999, 74, 3678-3680.	1.5	19
54	High-quality AlN grown on Si(111) by gas-source molecular-beam epitaxy with ammonia. Applied Physics Letters, 1999, 75, 484-486.	1.5	65

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55	Excitons bound to nitrogen clusters in GaAsN. Applied Physics Letters, 1999, 75, 1538-1540.	1.5	85
56	High quality GaN grown on Si(111) by gas source molecular beam epitaxy with ammonia. Applied Physics Letters, 1999, 75, 2073-2075.	1.5	194
57	Single and Double Variant Cupt-B Ordered GalnAs. Materials Research Society Symposia Proceedings, 1999, 583, 249.	0.1	1
58	X-ray Diffraction Study of Chalcopyrite ZnSnP2 Epitaxial Layers. Materials Research Society Symposia Proceedings, 1999, 583, 277.	0.1	0
59	High Quality AlN and GaN Grown on Si(111) by Gas Source Molecular Beam Epitaxy with Ammonia. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	1
60	Metalorganic molecular beam epitaxy of GaAsN with dimethylhydrazine. Applied Physics Letters, 1998, 72, 1999-2001.	1.5	20
61	Luminescence of as-grown and thermally annealed GaAsN/GaAs. Applied Physics Letters, 1998, 72, 1857-1859.	1.5	147
62	<title>Propagation of eigenmodes and transfer functions in waveguide WDM structures</title>. , 1998, , .		0